

NPN RF POWER TRANSISTOR

DESCRIPTION:

The **TPM401** is a Common Emitter Device Designed for Class A and AB Amplifier Applications up to 1.0 GHz.

FEATURES INCLUDE:

- High Gain
- Gold Metallization
- Emitter Ballasting

MAXIMUM RATINGS

I_C	400 mA
V_{CBO}	40 V
P_{DISS}	8.75 W @ T _C = 25 °C
T_J	-55 °C to +200 °C
T_{STG}	-55 °C to +200 °C
q_{JC}	20 °C/W

PACKAGE STYLE 280 4L STUD		
	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	1.010/25,65	1.055/26,80
B	.220/5,59	.230/5,84
C	.270/6,86	.285/7,24
D	.003/0,08	.007/0,18
E	.117/2,97	.137/3,48
F	.5/2/14,53	
G	.130/3,30	
H	.275/6,99	.285/7,24
I	.640/16,26	
J	.175/4,45	.21/75,51

1 = Collector
2 = Base

3 & 4 = Emitter

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 1.0 mA	40			V
BV_{CEO}	I _C = 1.0 mA	28			V
BV_{EBO}	I _E = 1.0 mA	3.5			V
h_{FE}	V _{CE} = 5.0 V I _C = 100 mA	20		120	---
C_{OB}	V _{CB} = 28 f = 1.0 MHz			5.0	pF
P_G	V _{CE} = 24 V I _C = 200 mA f = 400 MHz P _{OUT} = 1.0 W	13	15		dB
P_{1dB}	V _{CE} = 24 V I _C = 200 mA f = 400 MHz		2.0		W